

N-channel 40 V 2.1 mΩ standard level MOSFET 22 February 2013 P

Product data sheet

1. General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

3. Applications

- DC-to-DC convertors
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. C	uick reference data	1					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 3</u> ; <u>Fig. 1</u>		-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	306	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	[1]	-	1.75	2.1	mΩ
Dynamic ch	aracteristics						
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 80 A; V _{DS} = 20 V; Fig. 14; Fig. 15		-	25	-	nC

[1] Measured 3 mm from package.



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G L F A
mb	D	drain		mbb076 S
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PSMN2R2-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78					

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN2R2-40PS	PSMN2R2-40PS

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	40	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	100	А
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 3</u> ; <u>Fig. 1</u>	-	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3	-	1122	А

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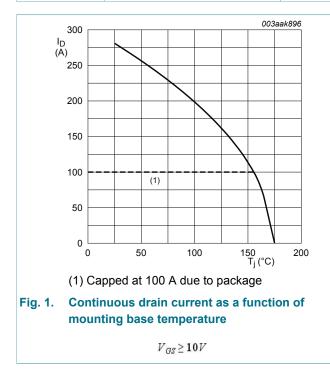
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Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	306	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	1122	А
Avalanche i	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{split} V_{GS} &= 10 \text{ V}; \text{T}_{j(\text{init})} = 25 ^\circ\text{C}; \text{I}_\text{D} = 100 \text{ A}; \\ V_{sup} &\leq 40 \text{ V}; \text{ unclamped}; \text{R}_{\text{GS}} = 50 \Omega \end{split}$	-	1.24	J



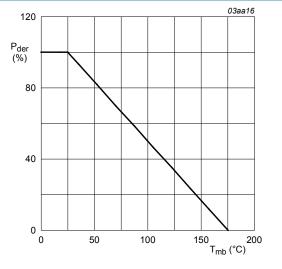


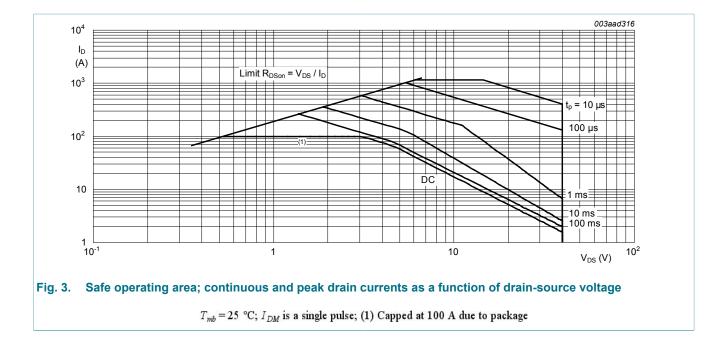
Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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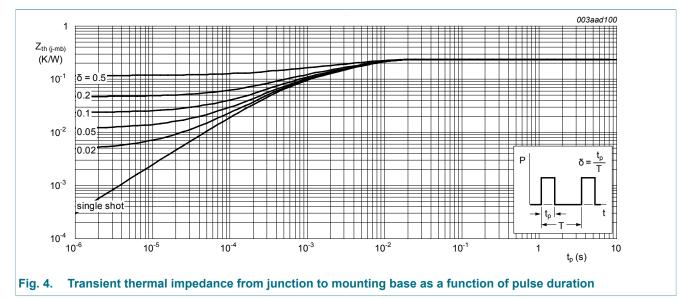
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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>4</u>	-	0.25	0.5	K/W



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10. Characteristics

Table 7. **Characteristics** Tested to JEDEC standards where applicable. **Symbol** Parameter **Conditions** Min Тур Max Unit Static characteristics drain-source I_D = 250 μA; V_{GS} = 0 V; T_i = -55 °C V 36 V_{(BR)DSS} _ breakdown voltage I_D = 250 μA; V_{GS} = 0 V; T_i = 25 °C V 40 _ - $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = -55 \text{ °C};$ gate-source threshold 4.6 V V_{GS(th)} -_ voltage Fig. 10 I_D = 1 mA; V_{DS} = V_{GS}; T_i = 175 °C; v 1 _ _ Fig. 10 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = 25 \text{ °C};$ 2 3 4 V Fig. 11; Fig. 10 V_{DS} = 40 V; V_{GS} = 0 V; T_i = 25 °C drain leakage current 10 μA _ IDSS -V_{DS} = 40 V; V_{GS} = 0 V; T_i = 125 °C 200 uА -_ V_{GS} = 20 V; V_{DS} = 0 V; T_i = 25 °C 100 nA gate leakage current I_{GSS} _ -V_{GS} = -20 V; V_{DS} = 0 V; T_i = 25 °C nA 100 - V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; drain-source on-state _ 2.4 2.85 mΩ R_{DSon} resistance Fig. 12; Fig. 13 V_{GS} = 10 V; I_D = 25 A; T_i = 175 °C; 3.25 3.9 mΩ -Fig. 12; Fig. 13 V_{GS} = 10 V; I_D = 25 A; T_i = 25 °C; 1.75 2.1 mΩ [1] -Fig. 12 R_{G} internal gate f = 1 MHz_ 1 _ Ω resistance (AC) **Dynamic characteristics** $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$ nC total gate charge 110 Q_{G(tot)} _ _ $I_D = 80 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ 130 nC -_ Fig. 14; Fig. 15 Q_{GS} gate-source charge 42 nC -_ pre-threshold gate-24 nC Q_{GS(th)} _ _ source charge post-threshold gate-18 nC Q_{GS(th-pl)} _ _ source charge gate-drain charge 25 nC Q_{GD} -_ V_{GS(pl)} gate-source plateau I_D = 80 A; V_{DS} = 20 V; <u>Fig. 14</u>; <u>Fig. 15</u> _ 4.95 -V voltage input capacitance V_{DS} = 20 V; V_{GS} = 0 V; f = 1 MHz; Ciss 8423 pF _ _

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 C_{oss}

T_i = 25 °C; <u>Fig. 16</u>

1671

-

output capacitance

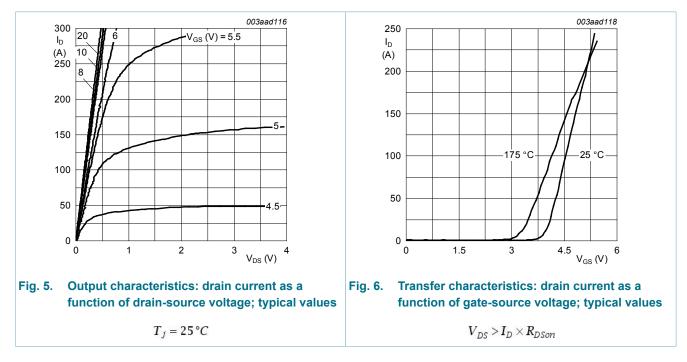
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C _{rss}	reverse transfer capacitance			-	814	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R _L = 0.25 Ω; V _{GS} = 10 V;		-	33.2	-	ns
t _r	rise time	$R_{G(ext)} = 1.5 \Omega$		-	40.4	-	ns
t _{d(off)}	turn-off delay time			-	66.6	-	ns
t _f	fall time	-		-	25.2	-	ns
Source-drain	diode					1	
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>		-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 25 A; dI_{S}/dt = -100 A/µs; V_{\rm GS} = 0 V; V_{\rm DS} = 20 V		-	53.7	-	ns
Q _r	recovered charge	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$		-	80.75	-	nC

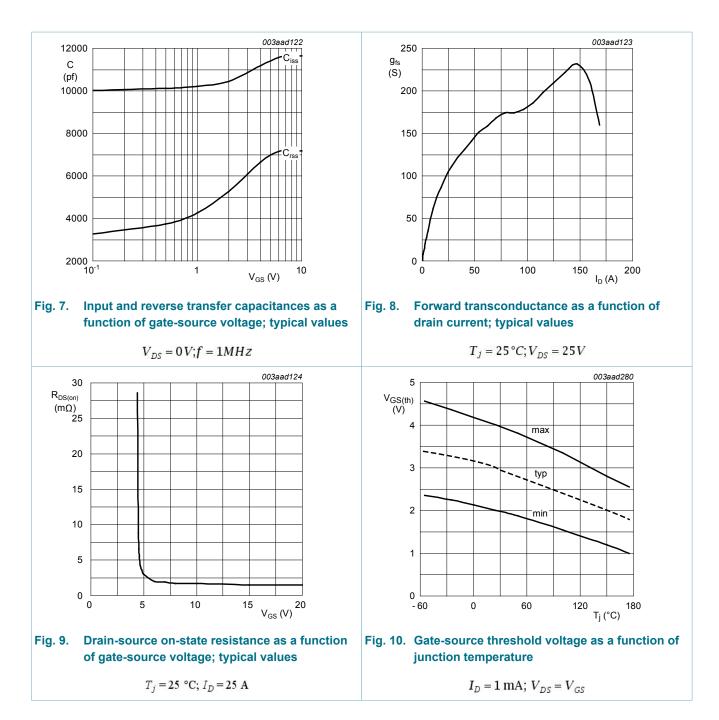
[1] Measured 3 mm from package.



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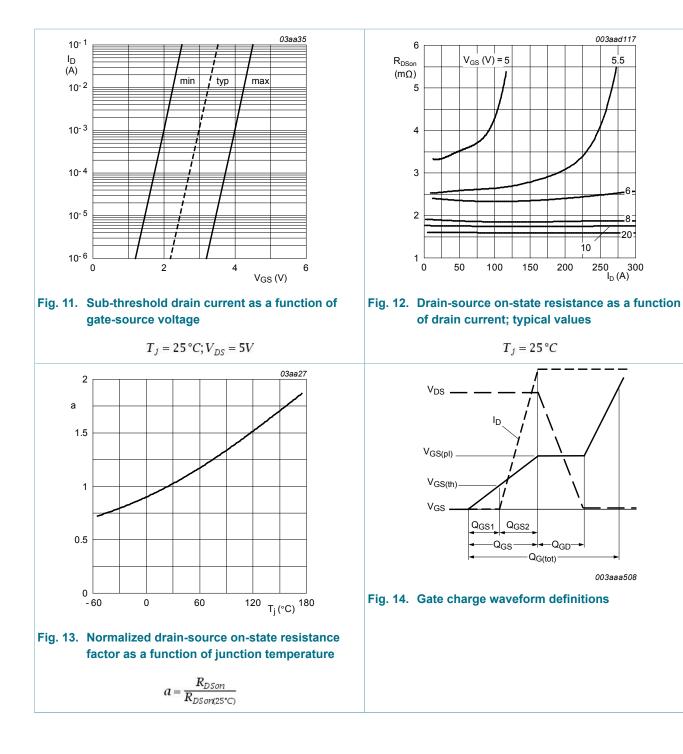
20

250 300 I_D (A)

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10

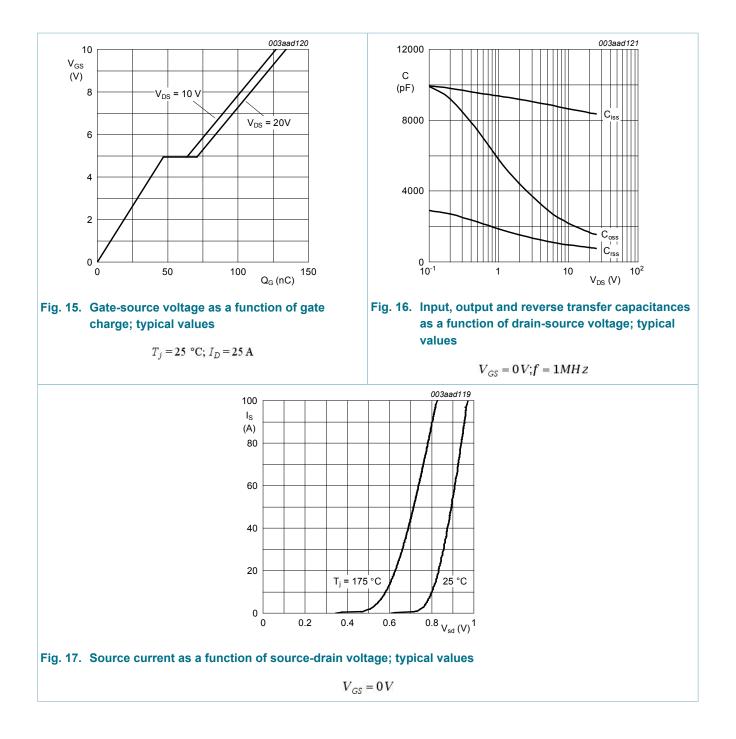
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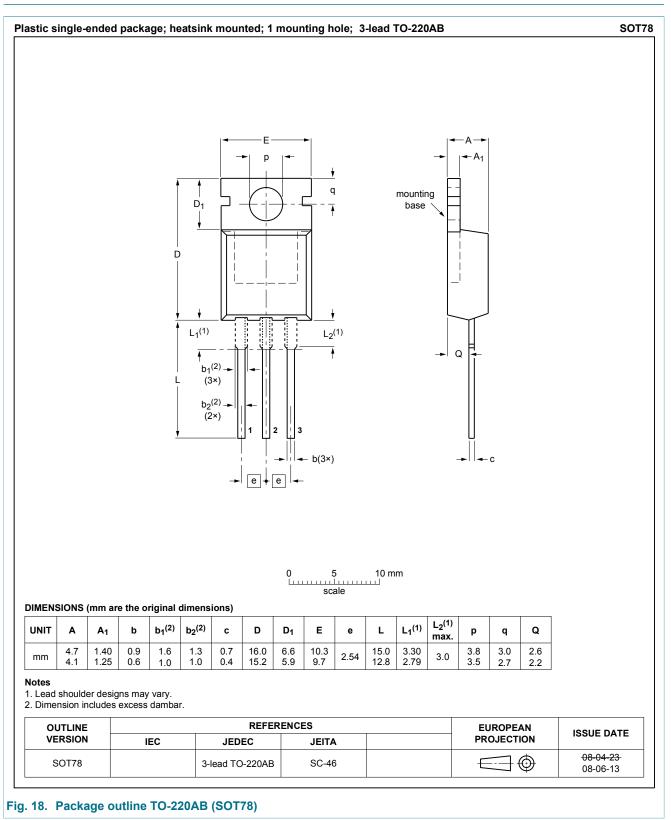
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11. Package outline



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Product data sheet

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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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